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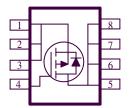
# P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	I <sub>D</sub> (A)	
	$60 @ V_{GS} = -4.5V$	-8.3	
-20	$80 @ V_{GS} = -2.5V$	-6.7	
	$150 @ V_{GS} = -1.8V$	-4.5	





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage		V <sub>DS</sub>	-20	v	
Gate-Source Voltage			±12	•	
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	T	-8.3		
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	ър	-6.7	А	
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	±50		
Continuous Source Current (Diode Conduction) <sup>a</sup>			-2.1	Α	
	T <sub>A</sub> =25°C	D	3.1	W	
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	$\begin{array}{c c} T_{A}=25^{\circ}C \\ \hline T_{A}=70^{\circ}C \end{array} P_{D} \end{array}$		vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	

HALOGEN

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum Un		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	р	40	°C/W	
	Steady-State	$R_{\theta JA}$	70	°C/W	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions	Limits			Unit	
Farameter			Min	Тур	Max	Umt	
Static							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-0.7				
Gate-Body Leakage	Igss	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			±100	nA	
Zero Gate Voltage Drain Current	Idss	$V_{DS} = -16 V, V_{GS} = 0 V$			-1	uA	
Zelo Gale voltage Diam Current		$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-5		
On-State Drain Current <sup>A</sup>	ID(on)	$V_{DS} = -4.5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -8.3 \text{ A}$			60		
Drain-Source On-Resistance <sup>A</sup>	fDS(on)	$V_{GS} = -2.5 \text{ V}, I_D = -6.7 \text{ A}$			80	mΩ	
		$V_{GS}$ = -1.8 V, $I_D$ = -4.5 A			150		
Forward Tranconductance <sup>A</sup>	$g_{\rm fs}$	$V_{DS} = -15 \text{ V}, I_D = -8.3 \text{ A}$		70		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_S = 2.5 A, V_{GS} = 0 V$		-0.6		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = -10 V$ , $V_{GS} = -4.5 V$ ,		16.7		nC	
Gate-Source Charge	Qgs	$V_{DS} = -10$ V, $V_{GS} = -4.5$ V, ID = -8.3 A		1.8			
Gate-Drain Charge	Qgd	ID = -0.5 A		1.9			
Turn-On Delay Time	$t_{d(on)}$			20			
Rise Time	tr	$V_{DD}$ = -10 V, $R_L$ = 6 $\Omega$ , ID = -1 A,		23		nS	
Turn-Off Delay Time	t <sub>d(off)</sub>	VGEN = -4.5 V		289			
Fall-Time	tf	]		134			

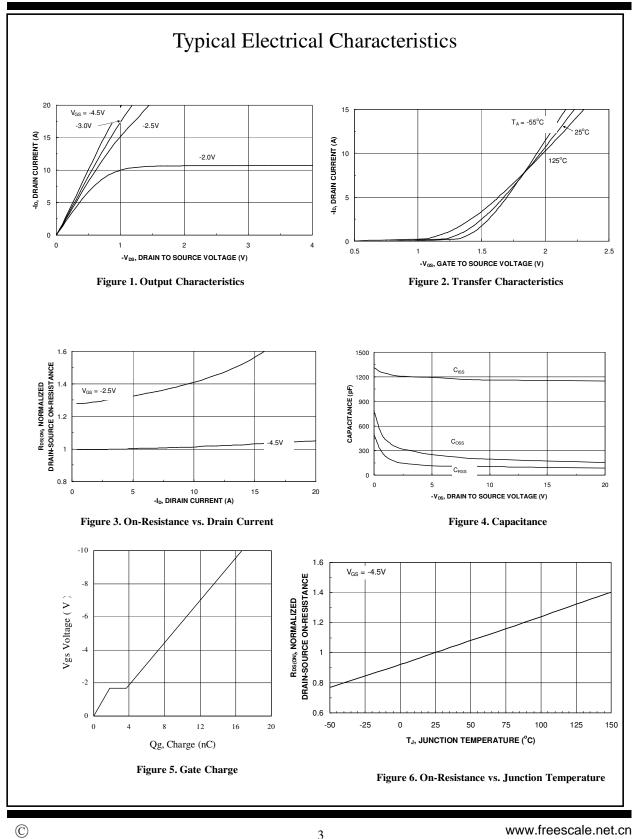
Notes

- a. Pulse test:  $PW \le 300$  us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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# Typical Electrical Characteristics

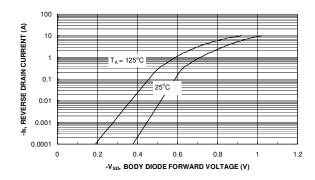


Figure 7. Source-Drain Diode Forward Voltage

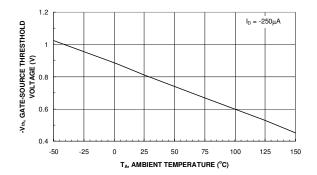


Figure 9. Vth Gate to Source Voltage Vs Temperature

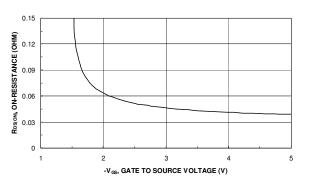


Figure 8. On-Resistance with Gate to Source Voltage

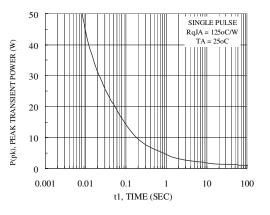
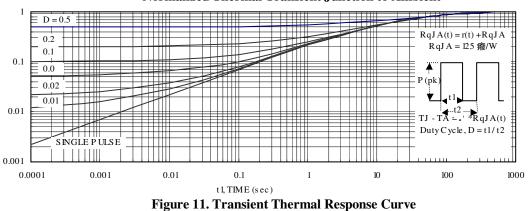


Figure 10. Single Pulse Maximum Power Dissipation



Normalized Thermal Transient Junction to Ambient

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